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# Low-Voltage 1.8/2.5/3.3V 16-Bit D-Type Flip-Flop

## With 3.6 V-Tolerant Inputs and Outputs (3-State, Non-Inverting)

The 74VCX16374 is an advanced performance, non-inverting 16-bit D-type flip-flop. It is designed for very high-speed, very low-power operation in 1.8 V, 2.5 V or 3.3 V systems. The VCX16374 is byte controlled, with each byte functioning identically, but independently. Each byte has separate Output Enable and Clock Pulse inputs. These control pins can be tied together for a full 16-bit operation.

When operating at 2.5 V (or 1.8 V) the part is designed to tolerate voltages it may encounter on either inputs or outputs when interfacing to 3.3 V busses. It is guaranteed to be overvoltage tolerant to 3.6 V.

The 74VCX16374 consists of 16 edge-triggered flip-flops with individual D-type inputs and 3.6 V-tolerant 3-state outputs. The clocks (CPn) and Output Enables ( $\overline{OEn}$ ) are common to all flip-flops within the respective byte. The flip-flops will store the state of individual D inputs that meet the setup and hold time requirements on the LOW-to-HIGH Clock (CP) transition. With the  $\overline{OE}$  LOW, the contents of the flip-flops are available at the outputs. When the  $\overline{OE}$  is HIGH, the outputs go to the high impedance state. The  $\overline{OE}$  input level does not affect the operation of the flip-flops.

#### **Features**

- Designed for Low Voltage Operation:  $V_{CC} = 1.65 \text{ V} 3.6 \text{ V}$
- 3.6 V Tolerant Inputs and Outputs
- High Speed Operation: 3.0 ns max for 3.0 V to 3.6 V

3.9 ns max for 2.3 V to 2.7 V

7.8 ns max for 1.65 V to 1.95 V

• Static Drive: ±24 mA Drive at 3.0 V

±18 mA Drive at 2.3 V

±6 mA Drive at 1.65 V

- Supports Live Insertion and Withdrawal
- $I_{OFF}$  Specification Guarantees High Impedance When  $V_{CC} = 0 V$
- Near Zero Static Supply Current in All Three Logic States (20 μA) Substantially Reduces System Power Requirements
- Latchup Performance Exceeds ±250 mA @ 125°C
- ESD Performance: Human Body Model >2000 V Machine Model >200 V
- All Devices in Package TSSOP are Inherently Pb-Free\*



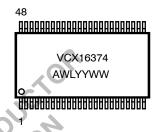
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## MARKING DIAGRAM



TSSOP-48 DT SUFFIX CASE 1201



A WL YY

- Assembly Location
- = Wafer Lot
  - = Year
- W = Work Week

#### **PIN NAMES**

Pins	Function
OEn CPn D0-D15 O0-O15	Output Enable Inputs Clock Pulse Inputs Inputs Outputs

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
74VCX16374DT	TSSOP (Pb-Free)	39 / Rail
74VCX16374DTR	TSSOP (Pb-Free)	2500 / Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

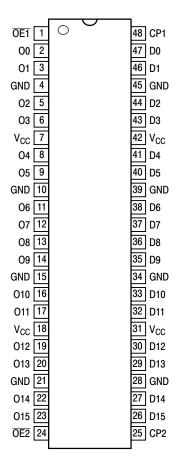
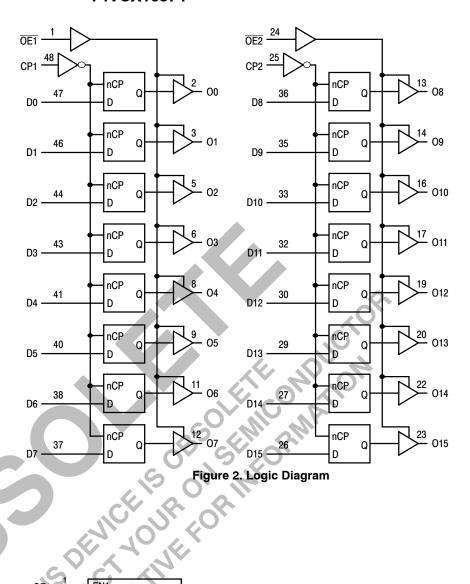


Figure 1. 48-Lead Pinout (Top View)



EN1 EN2 0E1 CP1 48 CP2 EN3 24 OE2 EN4 2 3 01 D0 1 V D1 46 D2 44 D3 43 D4 41 5 O2 6 03 2 ∇ 8 04 04 9 O5 40 D5  $\overline{D6} \frac{\overline{38}}{38}$ 11 O6 D0 37 D7 36 D8 36 12 O7 3 V 13 08 D9 35 14 O9 D9 33 D10 32 D11 30 D12 30 16 O10 17 011 4 ∇ 19 012 D13 29 20 O13 22 014 D14 27 23 O15 D15 26

Figure 3. IEC Logic Diagram

#### **TRUTH TABLE**

	Inputs		Outputs	Inputs			Outputs
CP1	OE1	D0:7	O0:7	CP2	OE2	D8:15	O8:15
1	L	Н	Н	1	L	Н	Н
1	L	L	L	1	L	L	L
Х	L	Х	O0	Х	L	Х	00
Х	Н	Х	Z	Х	Н	Х	Z

H = High Voltage Level

#### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Condition	Unit
V <sub>CC</sub>	DC Supply Voltage	-0.5 to +4.6		٧
VI	DC Input Voltage	$-0.5 \le V_{\parallel} \le +4.6$	.10	V
Vo	DC Output Voltage	$-0.5 \le V_0 \le +4.6$	Output in 3-State	V
		$-0.5 \le V_{O} \le V_{CC} + 0.5$	Note 1; Outputs Active	V
I <sub>IK</sub>	DC Input Diode Current	-50	V <sub>I</sub> < GND	mA
I <sub>OK</sub>	DC Output Diode Current	-50	Vo < GND	mA
		+50	V <sub>O</sub> > V <sub>CC</sub>	mA
I <sub>O</sub>	DC Output Source/Sink Current	±50		mA
I <sub>CC</sub>	DC Supply Current Per Supply Pin	±100	112	mA
I <sub>GND</sub>	DC Ground Current Per Ground Pin	±100		mA
T <sub>STG</sub>	Storage Temperature Range	−65 to +150		°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

#### RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Тур	Max	Unit
V <sub>CC</sub>	Supply Voltage Operating Data Retention Only		3.3 3.3	3.6 3.6	V
VI	Input Voltage	-0.3		3.6	V
V <sub>O</sub>	Output Voltage (Active State) (3-State)	0		V <sub>CC</sub> 3.6	V
I <sub>OH</sub>	HIGH Level Output Current, V <sub>CC</sub> = 3.0 V - 3.6 V			-24	mA
I <sub>OL</sub>	LOW Level Output Current, V <sub>CC</sub> = 3.0 V - 3.6 V			24	mA
I <sub>OH</sub>	HIGH Level Output Current, V <sub>CC</sub> = 2.3 V - 2.7 V			-18	mA
I <sub>OL</sub>	LOW Level Output Current, V <sub>CC</sub> = 2.3 V - 2.7 V			18	mA
I <sub>OH</sub>	HIGH Level Output Current, V <sub>CC</sub> = 1.65 V - 1.95 V			-6	mA
I <sub>OL</sub>	LOW Level Output Current, V <sub>CC</sub> = 1.65 V - 1.95 V			6	mA
T <sub>A</sub>	Operating Free-Air Temperature	-40		+85	°C
$\Delta t/\Delta V$	Input Transition Rise or Fall Rate, $V_{IN}$ from 0.8 V to 2.0 V, $V_{CC}$ = 3.0 V	0		10	ns/V

L = Low Voltage Level

Z = High Impedance State

<sup>↑</sup> Low-to-High Transition

X = High or Low Voltage Level and Transitions Are Acceptable, for I<sub>CC</sub> reasons, DO NOT FLOAT Inputs

O0 = No Change

<sup>1.</sup> I<sub>O</sub> absolute maximum rating must be observed.

#### DC ELECTRICAL CHARACTERISTICS

			T <sub>A</sub> = -40°	C to +85°C	
Symbol	Characteristic	Condition	Min	Max	Unit
V <sub>IH</sub>	HIGH Level Input Voltage (Note 2)	1.65 V ≤ V <sub>CC</sub> < 2.3 V	0.65 x V <sub>CC</sub>		V
		2.3 V ≤ V <sub>CC</sub> ≤ 2.7 V	1.6		
		2.7 V < V <sub>CC</sub> ≤ 3.6 V	2.0		
V <sub>IL</sub>	LOW Level Input Voltage (Note 2)	1.65 V ≤ V <sub>CC</sub> < 2.3 V		0.35 x V <sub>CC</sub>	V
		2.3 V ≤ V <sub>CC</sub> ≤ 2.7 V		0.7	
		2.7 V < V <sub>CC</sub> ≤ 3.6 V		0.8	]
V <sub>OH</sub>	HIGH Level Output Voltage	1.65 V ≤ $V_{CC}$ ≤ 3.6 V; $I_{OH}$ = −100 $\mu A$	V <sub>CC</sub> - 0.2		V
		V <sub>CC</sub> = 1.65 V; I <sub>OH</sub> = -6 mA	1.25		]
		$V_{CC} = 2.3 \text{ V}; I_{OH} = -6 \text{ mA}$	2.0		
		$V_{CC} = 2.3 \text{ V; } I_{OH} = -12 \text{ mA}$	1.8		
		V <sub>CC</sub> = 2.3 V; I <sub>OH</sub> = -18 mA	1.7	<b>1</b>	
		$V_{CC} = 2.7 \text{ V; } I_{OH} = -12 \text{ mA}$	2.2		
		$V_{CC} = 3.0 \text{ V}; I_{OH} = -18 \text{ mA}$	2.4		
		$V_{CC} = 3.0 \text{ V; } I_{OH} = -24 \text{ mA}$	2.2		
$V_{OL}$	LOW Level Output Voltage	1.65 V ≤ $V_{CC}$ ≤ 3.6 V; $I_{OL}$ = 100 $\mu$ A	4.10	0.2	V
		V <sub>CC</sub> = 1.65 V; I <sub>OL</sub> = 6 mA	.0	0.3	
		$V_{CC} = 2.3 \text{ V}; I_{OL} = 12 \text{ mA}$		0.4	
		V <sub>CC</sub> = 2.3 V; I <sub>OL</sub> = 18 mA		0.6	
		$V_{CC} = 2.7 \text{ V; } I_{OL} = 12 \text{ mA}$		0.4	
		V <sub>CC</sub> = 3.0 V; I <sub>OL</sub> = 18 mA		0.4	
		V <sub>CC</sub> = 3.0 V; I <sub>OL</sub> = 24 mA		0.55	
II	Input Leakage Current	$1.65 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \ 0 \text{ V} \le \text{V}_{\text{I}} \le 3.6 \text{ V}$		±5.0	μΑ
l <sub>OZ</sub>	3-State Output Current	$1.65 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; 0 \text{ V} \le \text{V}_{O} \le 3.6 \text{ V};$ $\text{V}_{I} = \text{V}_{IH} \text{ or V}_{IL}$		±10	μΑ
I <sub>OFF</sub>	Power-Off Leakage Current	V <sub>CC</sub> = 0 V; V <sub>I</sub> or V <sub>O</sub> = 3.6 V		10	μΑ
I <sub>CC</sub>	Quiescent Supply Current (Note 3)	1.65 V ≤ $V_{CC}$ ≤ 3.6 V; $V_{I}$ = GND or $V_{CC}$		20	μΑ
		$1.65 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; 3.6 \text{ V} \le \text{V}_{I}, \text{V}_{O} \le 3.6 \text{ V}$		±20	μΑ
$\Delta I_{CC}$	Increase in I <sub>CC</sub> per Input	2.7 V < V <sub>CC</sub> ≤ 3.6 V; V <sub>IH</sub> = V <sub>CC</sub> − 0.6 V		750	μΑ

<sup>2.</sup> These values of V<sub>I</sub> are used to test DC electrical characteristics only.
3. Outputs disabled or 3–state only.

#### AC CHARACTERISTICS (Note 4; $t_R = t_F = 2.0 \text{ ns}$ ; $C_L = 30 \text{ pF}$ ; $R_L = 500 \Omega$ )

					T <sub>A</sub> = -40	°C to +85°C	;		
			V <sub>CC</sub> = 3.0	V to 3.6 V	V <sub>CC</sub> = 2.3	V to 2.7 V	V <sub>CC</sub> = 1.65	V to 1.95 V	
Symbol	Parameter	Waveform	Min	Max	Min	Max	Min	Max	Unit
f <sub>max</sub>	Clock Pulse Frequency	1	250		200		100		MHz
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay CP-to-On	1	0.8 0.8	3.0 3.0	1.0 1.0	3.9 3.9	1.5 1.5	7.8 7.8	ns
t <sub>PZH</sub> t <sub>PZL</sub>	Output Enable Time to High and Low Level	2	0.8 0.8	3.5 3.5	1.0 1.0	4.6 4.6	1.5 1.5	9.2 9.2	ns
t <sub>PHZ</sub> t <sub>PLZ</sub>	Output Disable Time From High and Low Level	2	0.8 0.8	3.5 3.5	1.0 1.0	3.8 3.8	1.5 1.5	6.8 6.8	ns
t <sub>s</sub>	Setup Time, High or Low Dn-to-CP	3	1.5		1.5	<b>&gt;</b> .	2.5		ns
t <sub>h</sub>	Hold Time, High or Low Dn-to-CP	3	1.0		1.0		1.0		ns
t <sub>w</sub>	CP Pulse Width, High	3	1.5		1.5		4.0	1	ns
toshl toslh	Output-to-Output Skew (Note 5)			0.5 0.5		0.5 0.5	(C)	0.75 0.75	ns

<sup>4.</sup> For  $C_L = 50$  pF, add approximately 300 ps to the AC maximum specification.

#### AC CHARACTERISTICS ( $t_R = t_F = 2.0 \text{ ns}$ ; $C_L = 50 \text{ pF}$ ; $R_L = 500 \Omega$ )

				T <sub>A</sub> = -40°C to +85°C			
			V <sub>CC</sub> = 3.0	V to 3.6 V	V <sub>CC</sub> =	2.7 V	7
Symbol	Parameter	Waveform	Min	Max	Min	Max	Unit
f <sub>max</sub>	Clock Pulse Frequency	4	150	.0%	150		MHz
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay CP-to-On	4	1.0 1.0	4.2 4.2		4.9 4.9	ns
t <sub>PZH</sub> t <sub>PZL</sub>	Output Enable Time to High and Low Level	5	1.0 1.0	4.8 4.8		5.9 5.9	ns
t <sub>PHZ</sub> t <sub>PLZ</sub>	Output Disable Time From High and Low Level	5	1.0 1.0	4.3 4.3		4.7 4.7	ns
t <sub>OSHL</sub> t <sub>OSLH</sub>	Output-to-Output Skew (Note 6)	CO	S	0.5 0.5		0.5 0.5	ns

<sup>6.</sup> Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t<sub>OSHL</sub>) or LOW-to-HIGH (t<sub>OSLH</sub>); parameter guaranteed by design.

For C<sub>L</sub> = 50 pr, add approximately 500 ps to the AC maximum specification.
 Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device.
 The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t<sub>OSHL</sub>) or LOW-to-HIGH (t<sub>OSLH</sub>); parameter
 guaranteed by design.

#### **DYNAMIC SWITCHING CHARACTERISTICS**

			T <sub>A</sub> = +25°C	
Symbol	Characteristic	Condition	Тур	Unit
V <sub>OLP</sub>	Dynamic LOW Peak Voltage	$V_{CC}$ = 1.8 V, $C_L$ = 30 pF, $V_{IH}$ = $V_{CC}$ , $V_{IL}$ = 0 V	0.25	V
	(Note 7)	$V_{CC} = 2.5 \text{ V}, C_L = 30 \text{ pF}, V_{IH} = V_{CC}, V_{IL} = 0 \text{ V}$	0.6	
		$V_{CC} = 3.3 \text{ V}, C_L = 30 \text{ pF}, V_{IH} = V_{CC}, V_{IL} = 0 \text{ V}$	0.8	
V <sub>OLV</sub>	Dynamic LOW Valley Voltage	$V_{CC}$ = 1.8 V, $C_L$ = 30 pF, $V_{IH}$ = $V_{CC}$ , $V_{IL}$ = 0 V	-0.25	V
	(Note 7)	$V_{CC}$ = 2.5 V, $C_L$ = 30 pF, $V_{IH}$ = $V_{CC}$ , $V_{IL}$ = 0 V	-0.6	
		$V_{CC} = 3.3 \text{ V}, C_L = 30 \text{ pF}, V_{IH} = V_{CC}, V_{IL} = 0 \text{ V}$	-0.8	
V <sub>OHV</sub>	Dynamic HIGH Valley Voltage	$V_{CC} = 1.8 \text{ V}, C_L = 30 \text{ pF}, V_{IH} = V_{CC}, V_{IL} = 0 \text{ V}$	1.5	V
	(Note 8)	$V_{CC} = 2.5 \text{ V}, C_L = 30 \text{ pF}, V_{IH} = V_{CC}, V_{IL} = 0 \text{ V}$	1.9	
		$V_{CC} = 3.3 \text{ V}, C_L = 30 \text{ pF}, V_{IH} = V_{CC}, V_{IL} = 0 \text{ V}$	2.2	

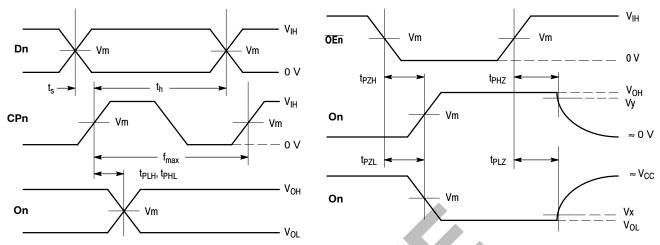
<sup>7.</sup> Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

#### **CAPACITIVE CHARACTERISTICS**

Symbol	Parameter	Condition Typical U	Unit
C <sub>IN</sub>	Input Capacitance	Note 9 6	pF
C <sub>OUT</sub>	Output Capacitance	Note 9 7	pF
C <sub>PD</sub>	Power Dissipation Capacitance	Note 9, 10 MHz 20 1	pF

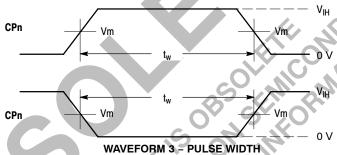
<sup>9.</sup>  $V_{CC} = 1.8 \text{ V}, 2.5 \text{ V or } 3.3 \text{ V}; V_I = 0 \text{ V or } V_{CC}.$ 

<sup>8.</sup> Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the HIGH state.



WAVEFORM 1 – PROPAGATION DELAYS, SETUP AND HOLD TIMES  $t_R = t_F = 2.0 \text{ ns}, \ 10\% \text{ to } 90\%; \ f = 1 \text{ MHz}; \ t_W = 500 \text{ ns} \\ t_R = t_F = 2.0 \text{ ns}, \ 10\% \text{ to } 90\%; \ f = 1 \text{ MHz}; \ t_W = 500 \text{ ns} \\ t_R = t_F = 2.0 \text{ ns}, \ 10\% \text{ to } 90\%; \ f = 1 \text{ MHz}; \ t_W = 500 \text{ ns} \\ t_R = t_F = 2.0 \text{ ns}, \ 10\% \text{ to } 90\%; \ f = 1 \text{ MHz}; \ t_W = 500 \text{ ns} \\ t_R = t_F = 2.0 \text{ ns}, \ 10\% \text{ to } 90\%; \ f = 1 \text{ MHz}; \ t_W = 500 \text{ ns} \\ t_R = t_F = 2.0 \text{ ns}, \ 10\% \text{ to } 90\%; \ f = 1 \text{ MHz}; \ t_W = 500 \text{ ns} \\ t_R = t_F = 2.0 \text{ ns}, \ 10\% \text{ to } 90\%; \ f = 1 \text{ MHz}; \ t_W = 500 \text{ ns} \\ t_R = t_F = 2.0 \text{ ns}, \ 10\% \text{ to } 90\%; \ f = 1 \text{ MHz}; \ t_W = 500 \text{ ns} \\ t_R = t_R = 0.0 \text{ ns}, \ 10\% \text{ to } 90\%; \ f = 1 \text{ MHz}; \ t_W = 500 \text{ ns} \\ t_R = t_R = 0.0 \text{ ns}, \ 10\% \text{ to } 90\%; \ f = 1 \text{ MHz}; \ t_W = 500 \text{ ns} \\ t_R = t_R = 0.0 \text{ ns}, \ 10\% \text{ to } 90\%; \ f = 1 \text{ MHz}; \ t_W = 500 \text{ ns} \\ t_R = 0.0 \text{ ns}, \ 10\% \text{ to } 90\%; \ f = 1 \text{ MHz}; \ t_W = 500 \text{ ns} \\ t_R = 0.0 \text{ ns}, \ 10\% \text{ to } 90\%; \ f = 1 \text{ MHz}; \ t_W = 500 \text{ ns} \\ t_R = 0.0 \text{ ns}, \ 10\% \text{ to } 90\%; \ f = 1 \text{ MHz}; \ t_W = 500 \text{ ns} \\ t_R = 0.0 \text{ ns}, \ 10\% \text{ to } 90\%; \ f = 1 \text{ MHz}; \ t_W = 500 \text{ ns} \\ t_R = 0.0 \text{ ns}, \ 10\% \text{ to } 90\%; \ f = 1 \text{ MHz}; \ t_W = 500 \text{ ns} \\ t_R = 0.0 \text{ ns}, \ 10\% \text{ to } 90\%; \ f = 1 \text{ MHz}; \ t_W = 500 \text{ ns} \\ t_R = 0.0 \text{ ns}, \ 10\% \text{ to } 90\%; \ f = 1 \text{ MHz}; \ t_W = 500 \text{ ns} \\ t_R = 0.0 \text{ ns}, \ 10\% \text{ to } 90\%; \ f = 1 \text{ MHz}; \ t_W = 500 \text{ ns} \\ t_R = 0.0 \text{ ns}, \ 10\% \text{ to } 90\%; \ f = 1 \text{ MHz}; \ t_W = 500 \text{ ns} \\ t_R = 0.0 \text{ ns}, \ 10\% \text{ to } 90\%; \ f = 1 \text{ MHz}; \ t_W = 500 \text{ ns} \\ t_R = 0.0 \text{ ns}, \ 10\% \text{ to } 90\%; \ f = 1 \text{ MHz}; \ t_W = 500 \text{ ns} \\ t_R = 0.0 \text{ ns}, \ 10\% \text{ to } 90\%; \ f_R = 0.0 \text{ to } 90\%; \ f_R = 0.0$ 

Figure 4. AC Waveforms



 $t_R = t_F = 2.0$  ns (or fast as required) from 10% to 90%

Figure 5. AC Waveforms

Table 1. AC WAVEFORMS

		V <sub>CC</sub>	
Symbol	3.3 V ± 0.3 V	2.5 V ± 0.2 V	1.8 V ± 0.15 V
V <sub>IH</sub>	2.7 V	V <sub>CC</sub>	V <sub>CC</sub>
V <sub>m</sub>	1.5 V	V <sub>CC</sub> /2	V <sub>CC</sub> /2
V <sub>x</sub>	V <sub>OL</sub> + 0.3 V	V <sub>OL</sub> + 0.15 V	V <sub>OL</sub> + 0.15 V
$V_{y}$	V <sub>OH</sub> – 0.3 V	V <sub>OH</sub> – 0.15 V	V <sub>OH</sub> – 0.15 V

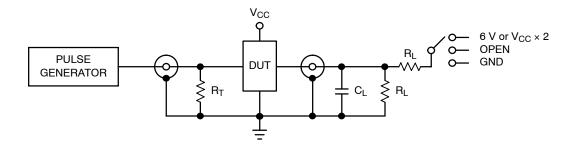


Figure 6. Test Circuit

#### **Table 2. TEST CIRCUIT**

TEST	SWITCH
PLH, <sup>t</sup> PHL	Open
t <sub>PZL</sub> , t <sub>PLZ</sub>	6 V at $V_{CC}$ = 3.3 ± 0.3 V; $V_{CC} \times$ 2 at $V_{CC}$ = 2.5 ± 0.2 V; 1.8 ± 0.15 V
t <sub>PZH</sub> , t <sub>PHZ</sub>	GND
$C_L=30~pF$ or equivalent (Includes jig and $R_L=500~\Omega$ or equivalent $R_T=Z_{OUT}$ of pulse generator (typically 50	

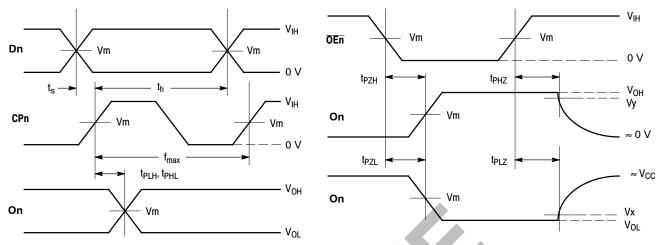
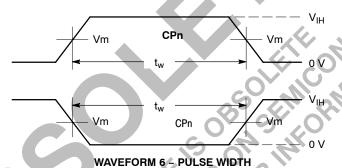


Figure 7. AC Waveforms



 $t_R = t_F = 2.0$  ns (or fast as required) from 10% to 90%

Figure 8. AC Waveforms

Table 3. AC WAVEFORMS

	V <sub>CC</sub>		
Symbol	3.3 V ± 0.3 V	2.7 V	
V <sub>IH</sub>	2.7 V	2.7 V	
V <sub>m</sub>	1.5 V	1.5 V	
V <sub>x</sub>	V <sub>OL</sub> + 0.3 V	V <sub>OL</sub> + 0.3 V	
$V_{y}$	V <sub>OH</sub> – 0.3 V	V <sub>OH</sub> – 0.3 V	

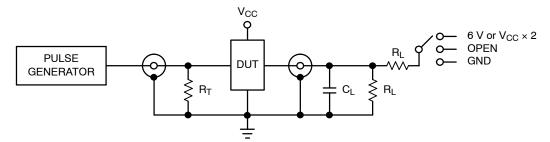


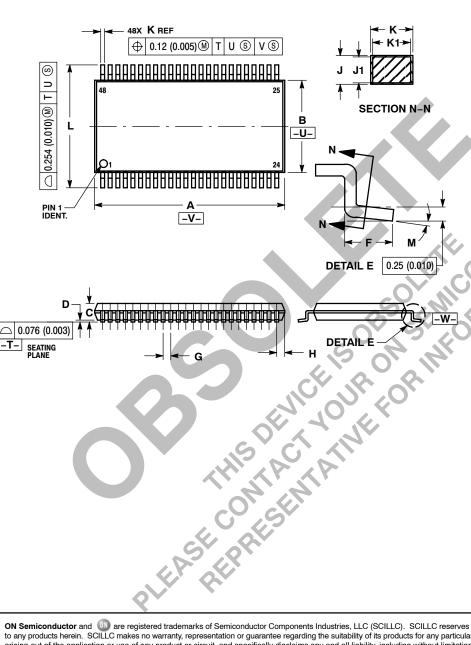
Figure 9. Test Circuit

**Table 4. TEST CIRCUIT** 

TEST	SWITCH	
t <sub>PLH</sub> , t <sub>PHL</sub>	Open	
t <sub>PZL</sub> , t <sub>PLZ</sub>	6 V at $V_{CC}$ = 3.3 ± 0.3 V; $V_{CC}$ × 2 at $V_{CC}$ = 2.5 ± 0.2 V; 1.8 ± 0.15 V	
t <sub>PZH</sub> , t <sub>PHZ</sub>	GND	
C <sub>L</sub> = 50 pF or equivalent (Includes jig and R <sub>L</sub> = 500 Ω or equivalent R <sub>T</sub> = Z <sub>OUT</sub> of pulse generator (typically 50 section 2).	Open 6 V at V <sub>CC</sub> = 3.3 ± 0.3 V; V <sub>CC</sub> × 2 at V <sub>CC</sub> = 2.5 ± 0.2 V; 1.8 ± 0.15 V  GND d probe capacitance)  ΩΩ)	

#### PACKAGE DIMENSIONS

#### **TSSOP DT SUFFIX** CASE 1201-01 **ISSUE A**



#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: MILLIMETER.
  3. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

  4. DIMENSION K DOES NOT INCLUDE DAMBAR
- PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION
- TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
  DIMENSIONS A AND B ARE TO BE
  DETERMINED AT DATUM PLANE -W-

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	12.40	12.60	0.488	0.496
В	6.00	6.20	0.236	0.244
C		1.10		0.043
D	0.05	0.15	0.002	0.006
E	0.50	0.75	0.020	0.030
G	0.50 BSC		0.0197 BSC	
Η,	0.37		0.015	
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.17	0.27	0.007	0.011
K1	0.17	0.23	0.007	0.009
L	7.95	8.25	0.313	0.325
M	0 °	8 °	0 °	8°

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